Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO247 plastic package





2. Features and benefits

- Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- · Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by Epoxy Mold Compound

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	tes Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			650			V
I _{F(AV)}	average forward current	δ = 0.5; $T_{mb} \le$ 113 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		80			А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 113 °C; square-wave pulse		160			А
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		500		А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		550		А	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 80 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.20	2.70	V
		I _F = 80 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.60	2.10	V
Dynamic	characteristics					,	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_i = 25 \text{ °C}$; Fig. 7		- 39 -		ns	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K 1/1 A
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathode	K A TO247-2L	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC80MW-650PST2	TO247-2L	BYC80MW-650PST2Q	Tube	30	TO247L-2L (L)	10-Nov-2020
					TO247P-2L (P)	09-Mar-2023

7. Marking

Table 4. Marking codes

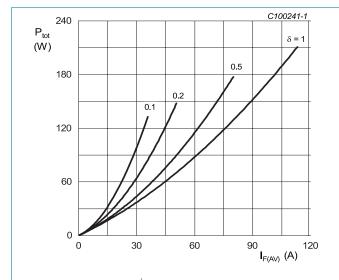
Type number	Marking codes	
	Assembly factory: L	Assembly factory: P
BYC80MW-650PST2	BYC80MW 650PST2 PJLxxxx xx	BYC80MW 650PST2 PJPxxxx xx

8. Limiting values

Table 5. Limiting values

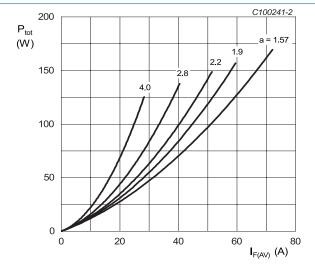
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 113 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		80	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 113 °C; square-wave pulse		160	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		500	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		550	Α
T _{stg}	storage temperature			-65 to 175	°C
Tj	junction temperature			-65 to 175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.009 \text{ V}; R_s = 0.0076 \Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; typical values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.009 V; R_s = 0.0076 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; typical values

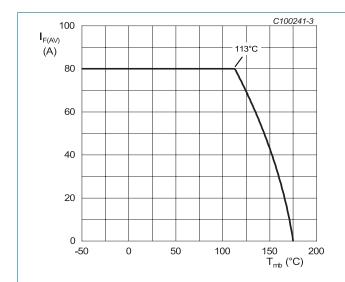


Fig. 3. Average forward current as a function of mounting base temperature; typical values

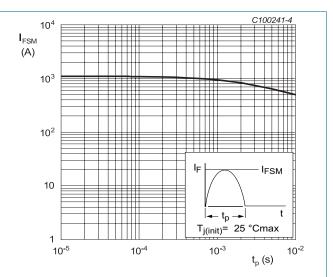


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 5		-	-	0.43	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

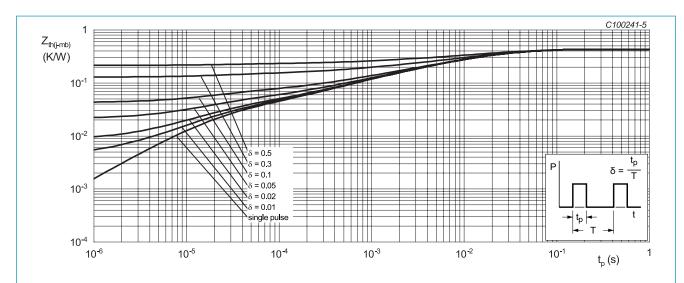
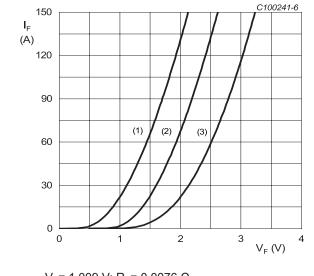


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 75 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.05	2.50	V
		I _F = 75 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.55	2.00	V
		I _F = 80 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.20	2.70	V
		I _F = 80 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.60	2.10	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.8	30	μΑ
		V _R = 650 V; T _j = 150 °C		-	0.2	5	mA
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	299	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	1140	-	nC
t _{rr} r	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	39	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	63	-	ns
		I_F = 50 A; V_R = 400 V; dI_F/dt = 500 A/ μ s; T_j = 125 °C; Fig. 7		-	108	-	ns
I _{RM}	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	9.5	-	А
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	21	-	А
E _{as}	non-repetitive avalanche energy	T _{j(init)} = 25 °C		30	-	-	mJ



 V_o = 1.009 V; R_s = 0.0076 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

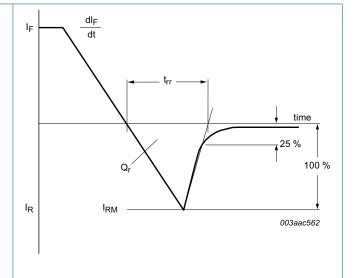


Fig. 7. Reverse recovery definitions; ramp recovery

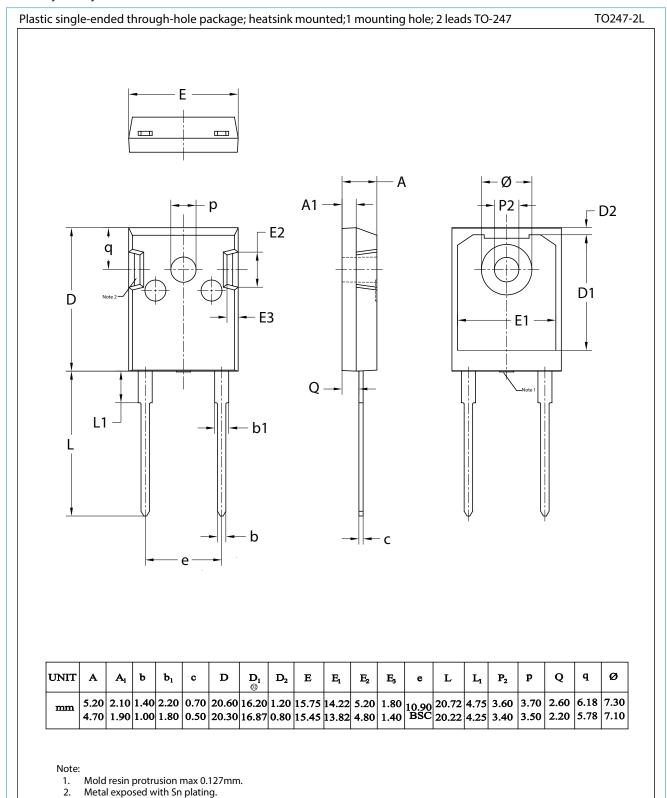
BYC80MW-650PST2

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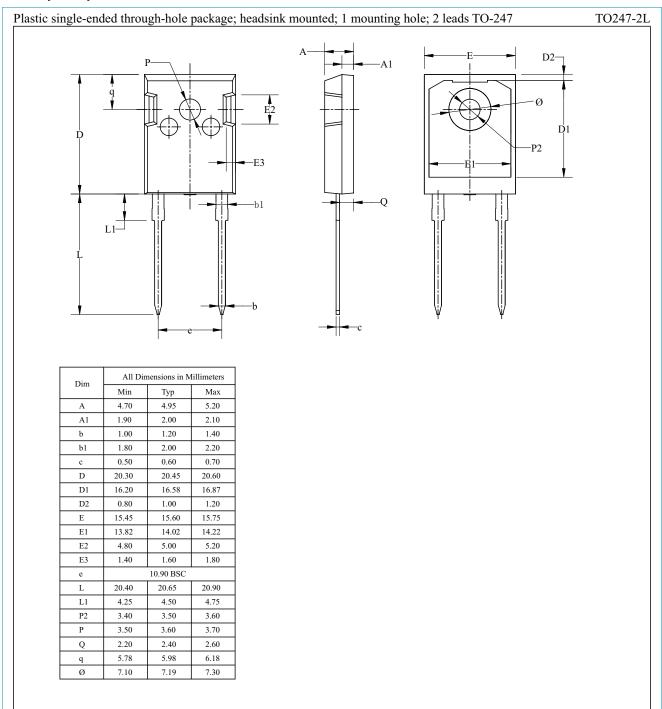
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11. Package outline

Assembly factory: L



Assembly factory: P



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For sales office addresses, please send an email to: salesaddresses@ween-semi.com
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